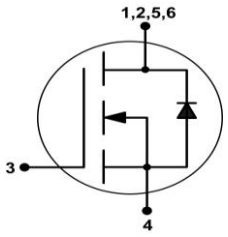
OptiMOS™2 Small-Signal-Transistor

Features

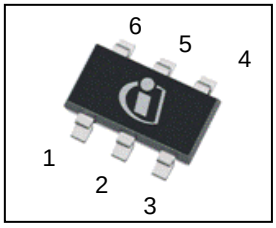
- N-channel
- Enhancement mode
- Ultra Logic level (1.8V rated)
- Avalanche rated
- Qualified according to AEC Q101
- 100% lead-free; RoHS compliant
- Halogen free according to IEC61249-2-21

Product Summary

V_{DS}		20	V
$R_{DS(on),max}$	V_{GS}=2.5 V	22	mΩ
	V_{GS}=1.8 V	31	
I_D		7.5	A



PG-TSOP6



Type	Package	Tape and Reel Information	Marking	Lead Free	Packing
BSL802SN	PG-TSOP6	H6327: 3000 pcs/ reel	sPP	Yes	Non dry

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_A=25 °C	7.5	A
		T_A=70 °C	6.0	
Pulsed drain current	$I_{D,pulse}$	T_A=25 °C	30	
Avalanche energy, single pulse	E_{AS}	I_D=7.5 A, R_{GS}=25 Ω	30	mJ
Reverse diode dv/dt	dv/dt	I_D=7.5 A, V_{DS}=16 V, di/dt=200 A/µs, $T_{j,max}$=150 °C	6	kV/µs
Gate source voltage	V_{GS}		±8	V
Power dissipation [1)]	P_{tot}	T_A=25 °C	2	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
ESD Class		JESD22-A114 -HBM	0 (<250V)	
Soldering Temperature			260 °C	
IEC climatic category; DIN IEC 68-1			55/150/56	

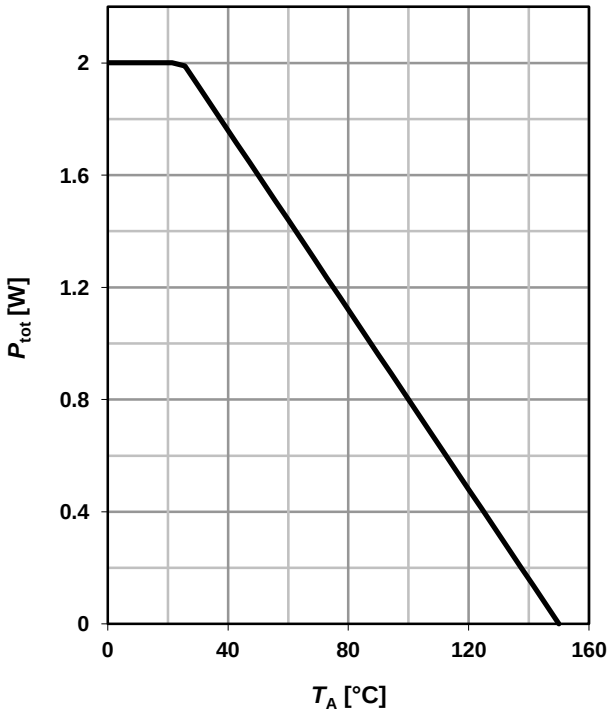
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - minimal footprint	R_{thJS}		-	-	50	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	230	
		6 cm^2 cooling area[1)]	-	-	62.5	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}= 0 V, I_D= 250 µA	20	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=30 µA	0.3	0.55	0.75	
Drain-source leakage current	I_{DSS}	V_{DS}=20 V, V_{GS}=0 V, T_j=25 °C	-	-	1	µA
		V_{DS}=20 V, V_{GS}=0 V, T_j=150 °C	-	-	100	
Gate-source leakage current	I_{GSS}	V_{GS}=8 V, V_{DS}=0 V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=1.8 V, I_D=3.6 A	-	23	31	mΩ
		V_{GS}=2.5 V, I_D=7.5 A	-	18	22	
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=6 A		25	-	S

[1)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (single layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air. (t < 5 sec.)

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=10 V, f=1 MHz	-	1013	1347	pF
Output capacitance	C_{oss}		-	290	385	
Reverse transfer capacitance	C_{rss}		-	51	77	
Turn-on delay time	$t_{d(on)}$	V_{DD}=10 V, V_{GS}=2.5 V, I_D=3.7 A, $R_{G,ext}$=6 Ω	-	10	-	ns
Rise time	t_r		-	30	-	
Turn-off delay time	$t_{d(off)}$		-	20	-	
Fall time	t_f		-	5.5	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=10 V, I_D=7.5 A, V_{GS}=0 to 2.5 V	-	1.6	-	nC
Gate to drain charge	Q_{gd}		-	1.6	-	
Gate charge total	Q_g		-	4.7	-	
Gate plateau voltage	$V_{plateau}$		-	1.5	-	V
Reverse Diode						
Diode continous forward current	I_S	T_A=25 °C	-	-	1.8	A
Diode pulse current	$I_{S,pulse}$		-	-	30	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=7.5 A, T_j=25 °C	-	0.86	1.1	V
Reverse recovery time	t_{rr}	V_R=10 V, I_F=7.5 A, di_F/dt=100 A/µs	-	15	-	ns
Reverse recovery charge	Q_{rr}		-	5.1	-	nC

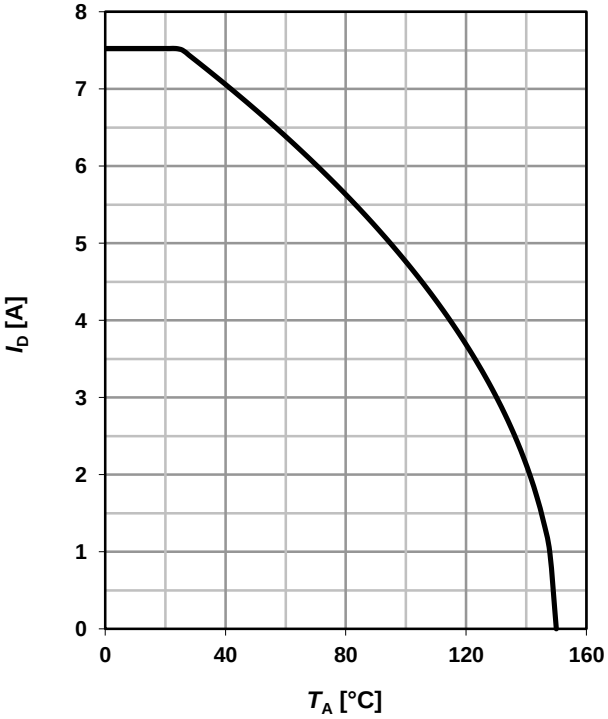
1 Power dissipation

$P_{tot}=f(T_A)$



2 Drain current

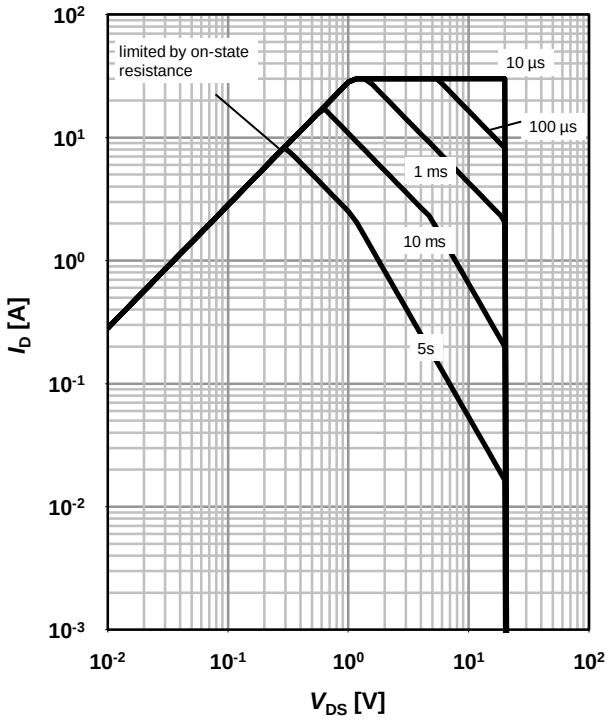
$I_D=f(T_A)$; $V_{GS}\geq 2.5$ V



3 Safe operating area

$I_D=f(V_{DS})$; T_A=25 °C; D=0

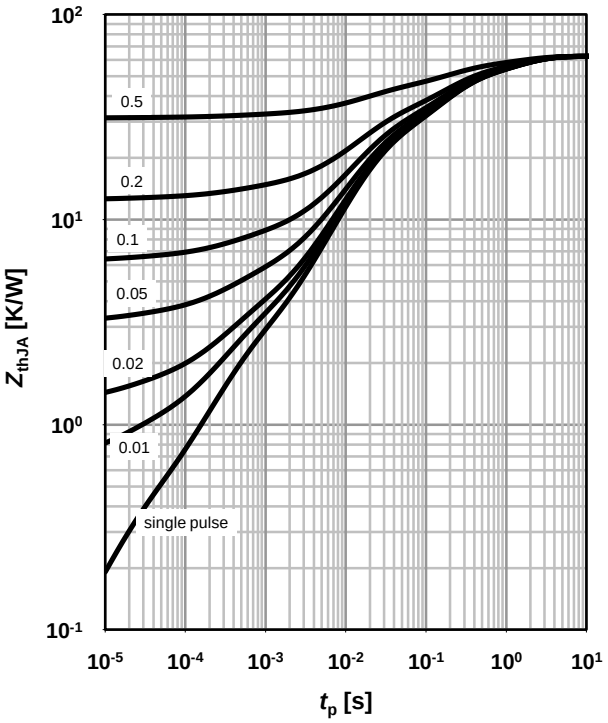
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJA}=f(t_p)$

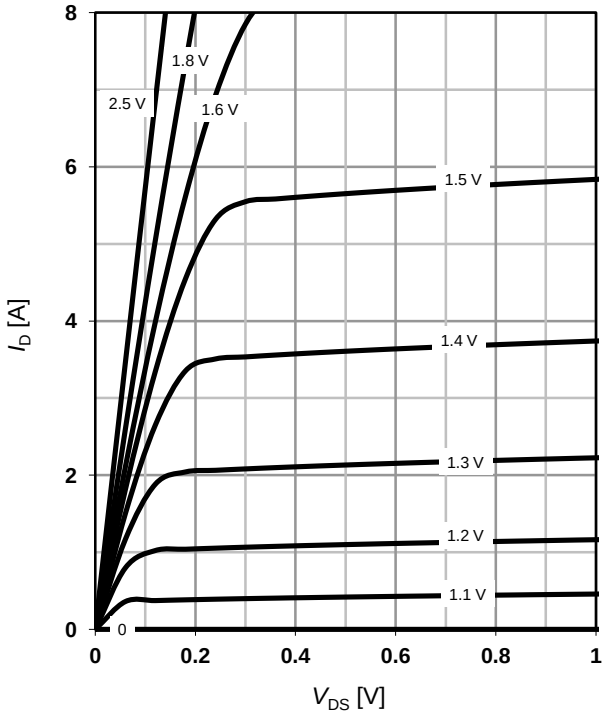
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D=f(V_{DS})$; $T_j=25$ °C

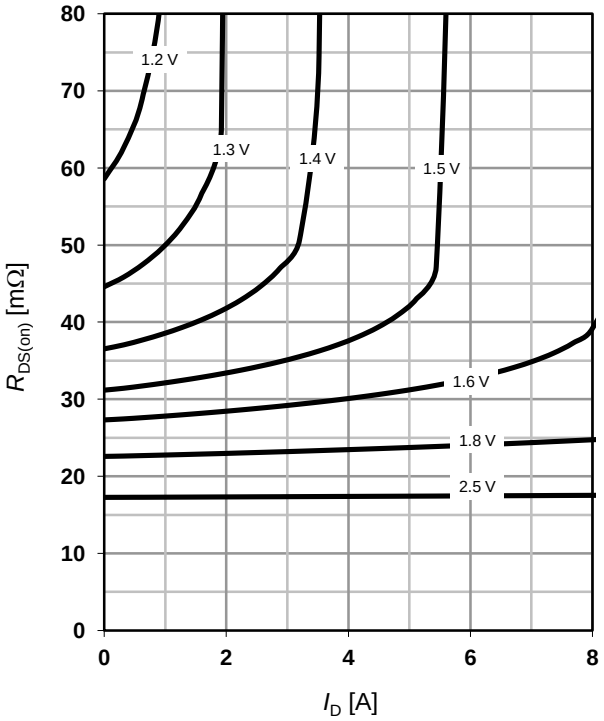
parameter: V_{GS}



6 Typ. drain-source on resistance

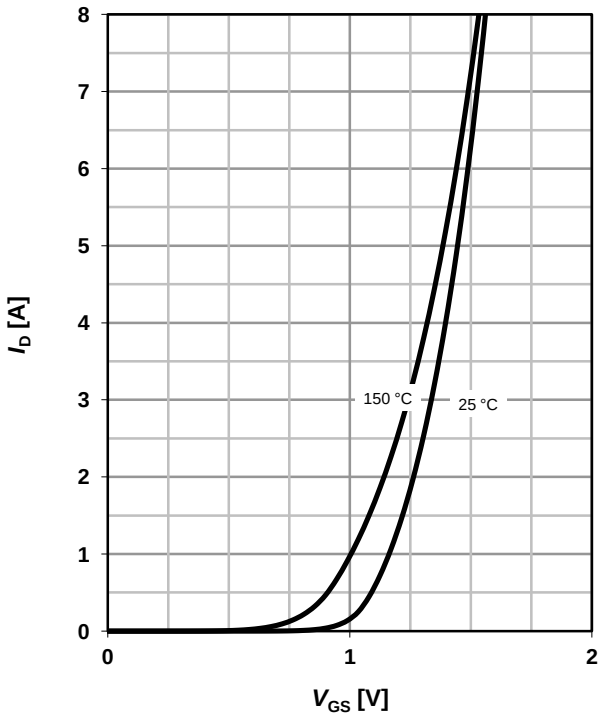
$R_{DS(on)}=f(I_D)$; $T_j=25$ °C

parameter: V_{GS}



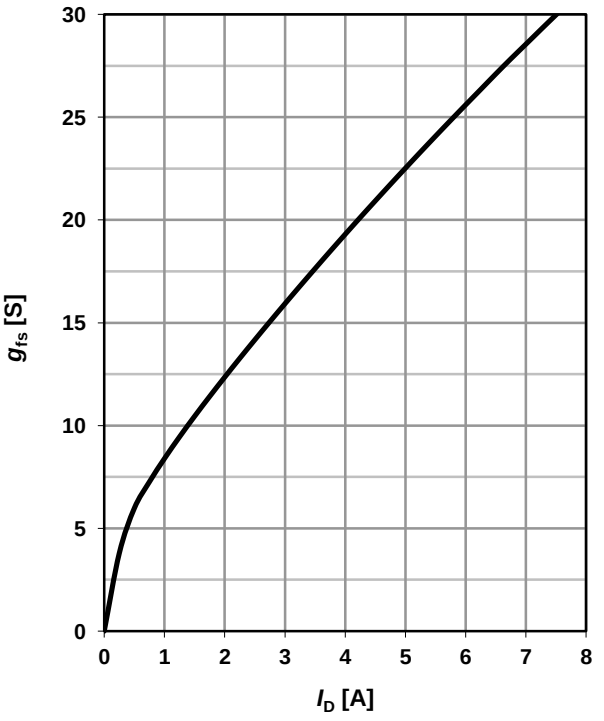
7 Typ. transfer characteristics

$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$



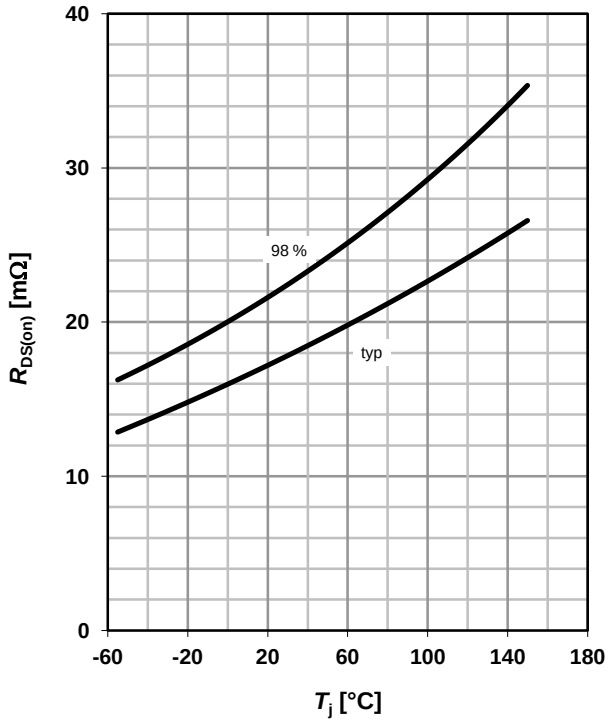
8 Typ. forward transconductance

$g_{fs}=f(I_D)$; $T_j=25$ °C



9 Drain-source on-state resistance

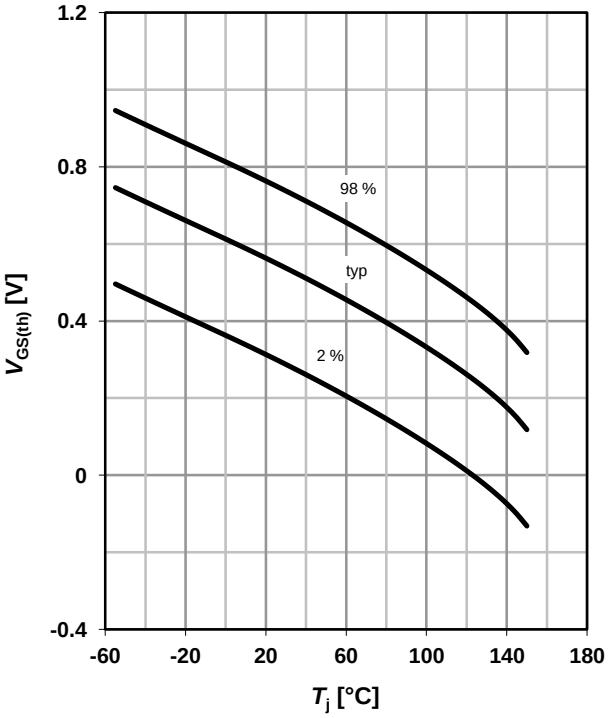
$R_{DS(on)}$=f(T_j); I_D=7.5 A; V_{GS}=2.5 V



10 Typ. gate threshold voltage

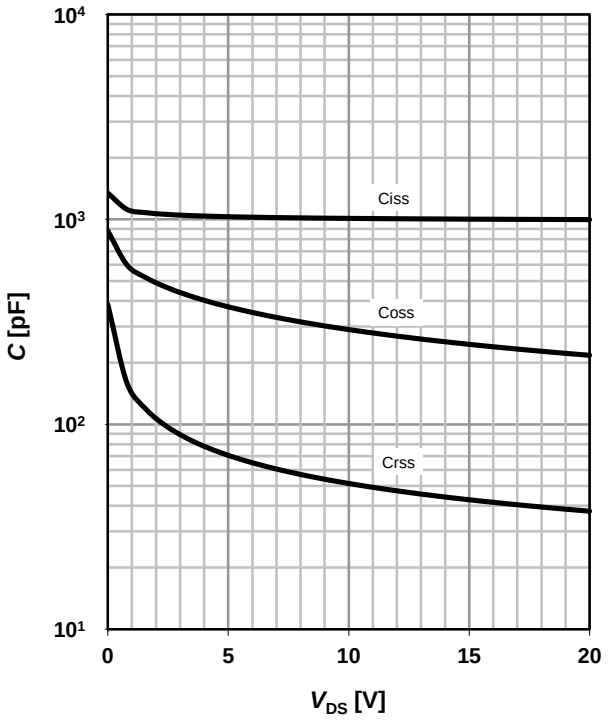
$V_{GS(th)}$=f(T_j); V_{DS}=V_{GS}; I_D=30 µA

parameter: I_D



11 Typ. capacitances

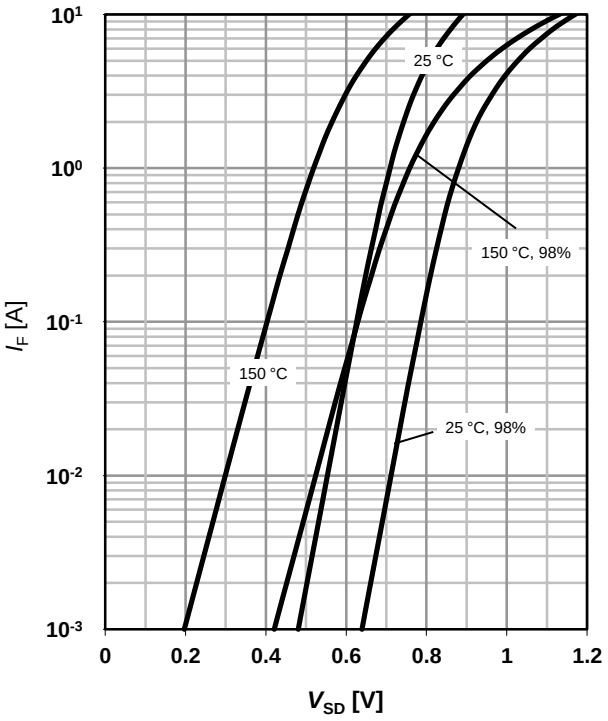
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz; T_j=25°C



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

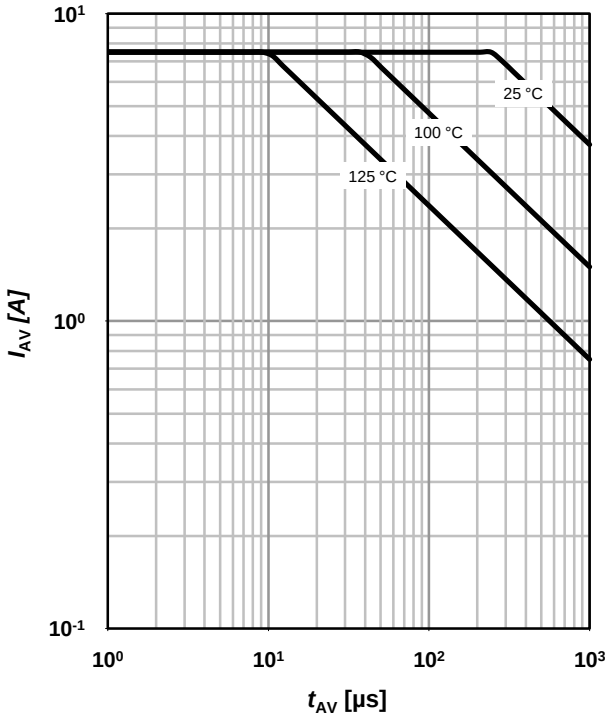
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

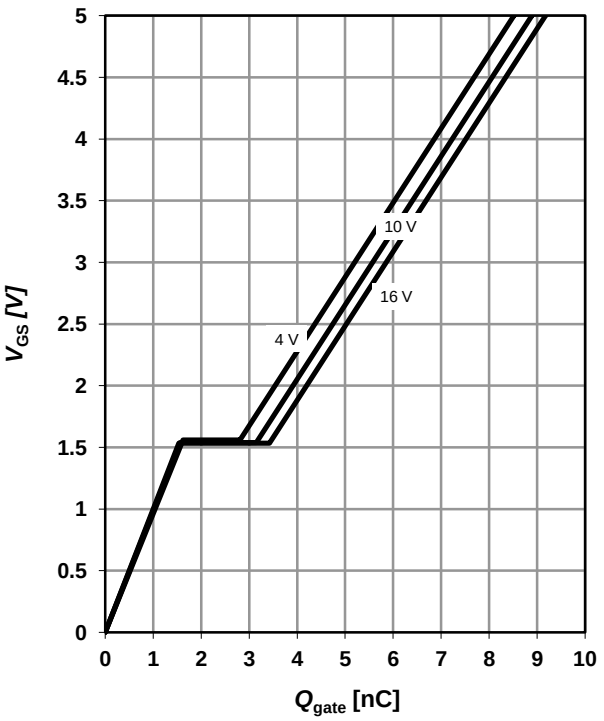
parameter: $T_{j(start)}$



14 Typ. gate charge

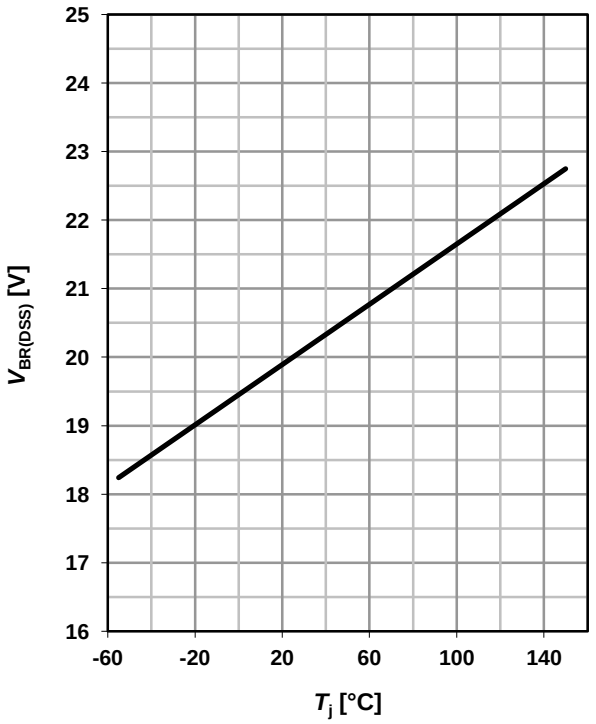
V_{GS}=f(Q_{gate}); I_D=7.5 A pulsed

parameter: V_{DD}

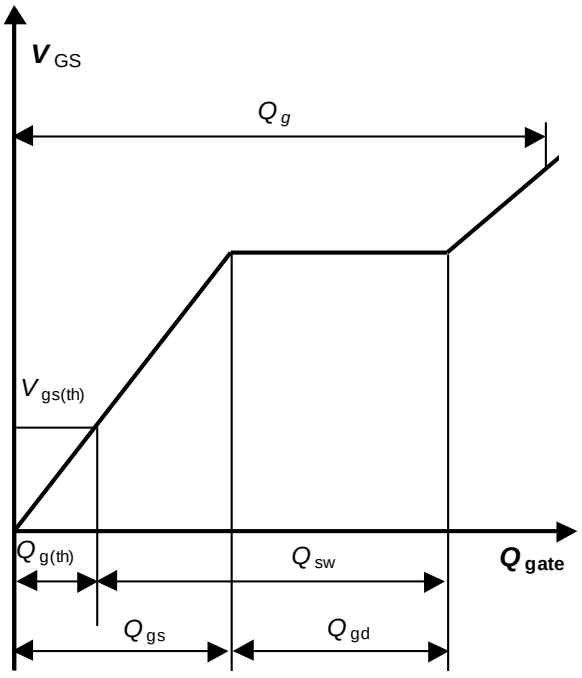


15 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=250 µA

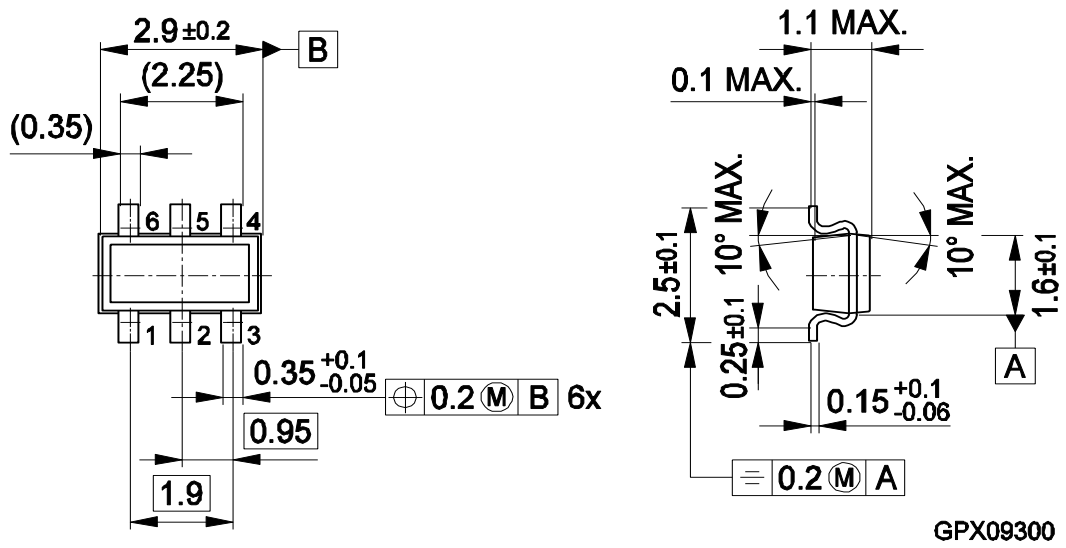


16 Gate charge waveforms

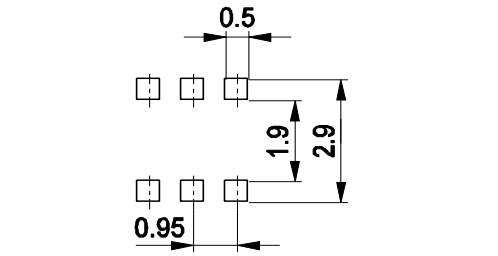


TSOP6

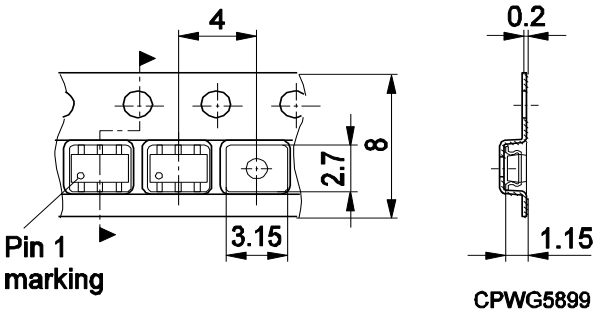
Package Outline:



Footprint:



Packaging:



Dimensions in mm

Published by
Infineon Technologies AG
81726 Munich, Germany

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